

# IRFS4115-7PPbF

HEXFET® Power MOSFET

## Applications

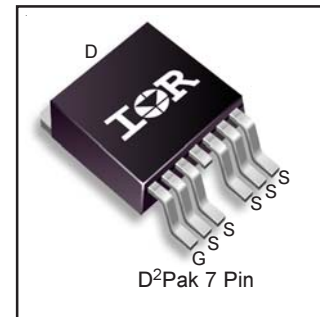
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

## Benefits

- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode  $dV/dt$  and  $dI/dt$  Capability
- Lead-Free



$V_{DSS}$	<b>150V</b>
$R_{DS(on)}$ <b>typ.</b>	<b>10.0mΩ</b>
	<b>max</b>
$I_D$	<b>105A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

## Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	105	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	74	
$I_{DM}$	Pulsed Drain Current ①	420	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	380	W
	Linear Derating Factor	2.5	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$dv/dt$	Peak Diode Recovery ③	32	V/ns
$T_J$	Operating Junction and	-55 to +175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

## Avalanche Characteristics

$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	230	mJ
$I_{AR}$	Avalanche Current ①	See Fig. 14, 15, 22a, 22b,	A
$E_{AR}$	Repetitive Avalanche Energy ④		mJ

## Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧⑨	—	0.40	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦⑧	—	40	

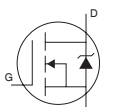
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	150	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.18	—	V/°C	Reference to 25°C, I <sub>D</sub> = 3.5mA <sup>①</sup>
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	10.	11.8	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 63A <sup>④</sup>
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
R <sub>G(int)</sub>	Internal Gate Resistance	—	2.1	—	Ω	

**Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	93	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 62A
Q <sub>g</sub>	Total Gate Charge	—	73	110	nC	I <sub>D</sub> = 63A
Q <sub>gs</sub>	Gate-to-Source Charge	—	28	—		V <sub>DS</sub> = 75V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	28	—		V <sub>GS</sub> = 10V <sup>④</sup>
Q <sub>sync</sub>	Total Gate Charge Sync. (Q <sub>g</sub> - Q <sub>gd</sub> )	—	45	—		I <sub>D</sub> = 63A, V <sub>DS</sub> = 0V, V <sub>GS</sub> = 10V
t <sub>d(on)</sub>	Turn-On Delay Time	—	18	—	ns	V <sub>DD</sub> = 98V
t <sub>r</sub>	Rise Time	—	50	—		I <sub>D</sub> = 63A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	37	—		R <sub>G</sub> = 2.1Ω
t <sub>f</sub>	Fall Time	—	23	—		V <sub>GS</sub> = 10V <sup>④</sup>
C <sub>iss</sub>	Input Capacitance	—	5320	—		V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	490	—		V <sub>DS</sub> = 50V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	110	—	pF	f = 1.0MHz
C <sub>oss eff. (ER)</sub>	Effective Output Capacitance (Energy Related) <sup>⑥</sup>	—	450	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 120V <sup>⑥</sup>
C <sub>oss eff. (TR)</sub>	Effective Output Capacitance (Time Related) <sup>⑤</sup>	—	520	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 120V <sup>⑤</sup>

**Diode Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	104	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) <sup>①</sup>	—	—	420		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 63A, V <sub>GS</sub> = 0V <sup>④</sup>
t <sub>rr</sub>	Reverse Recovery Time	—	82	—	ns	T <sub>J</sub> = 25°C V <sub>R</sub> = 130V, T <sub>J</sub> = 125°C I <sub>F</sub> = 63A
Q <sub>rr</sub>	Reverse Recovery Charge	—	271	—	nC	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C
I <sub>RRM</sub>	Reverse Recovery Current	—	6.0	—	A	T <sub>J</sub> = 25°C
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 0.115mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 63A, V<sub>GS</sub> = 10V. Part not recommended for use above this value.
- ③ I<sub>SD</sub> ≤ 63A, di/dt ≤ 2510A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑤ C<sub>oss eff. (TR)</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DSS</sub>.
- ⑥ C<sub>oss eff. (ER)</sub> is a fixed capacitance that gives the same energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DSS</sub>.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧ R<sub>θj</sub> is measured at T<sub>J</sub> approximately 90°C.
- ⑨ R<sub>θJC</sub> value shown is at time zero.

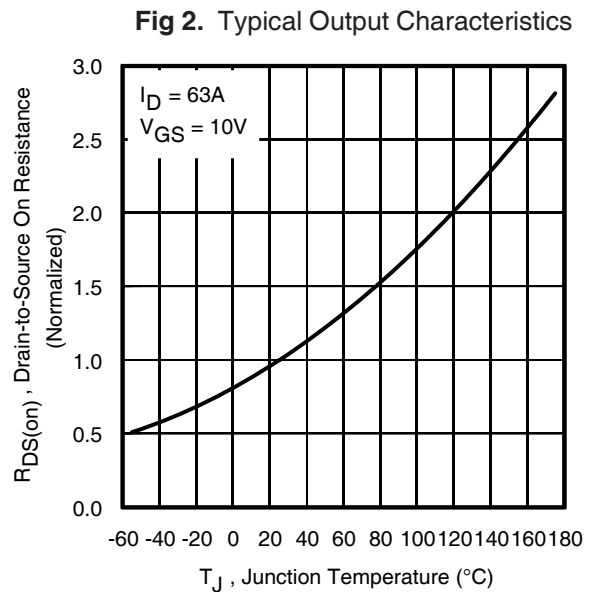
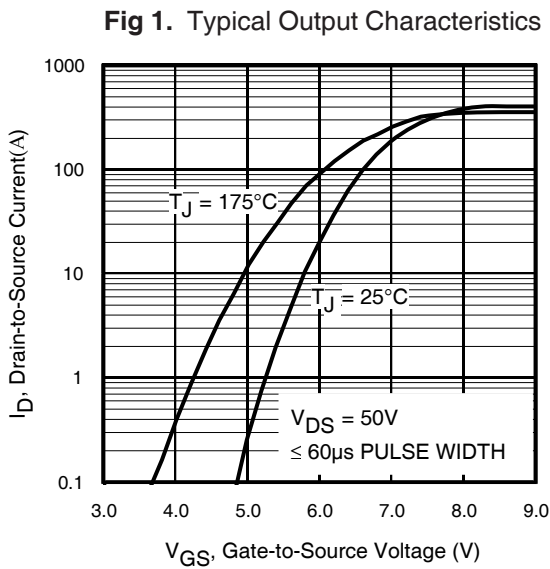
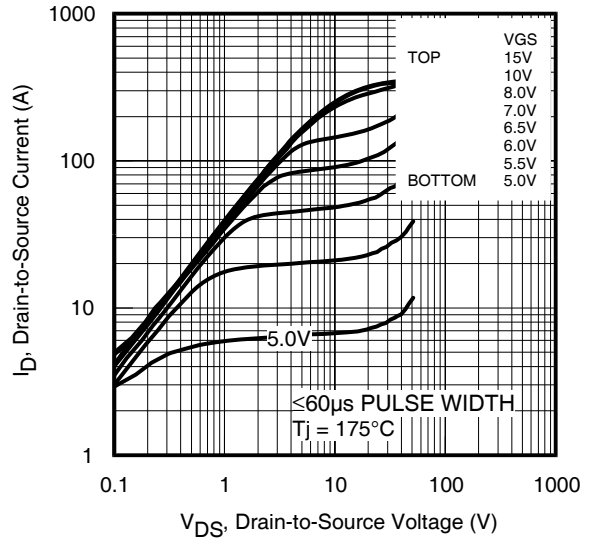
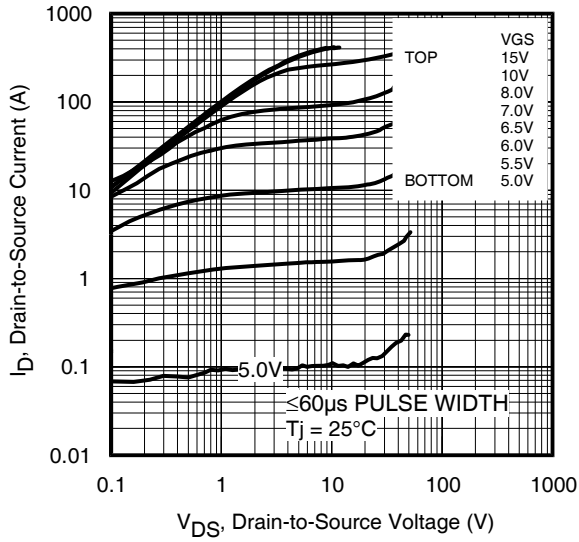


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

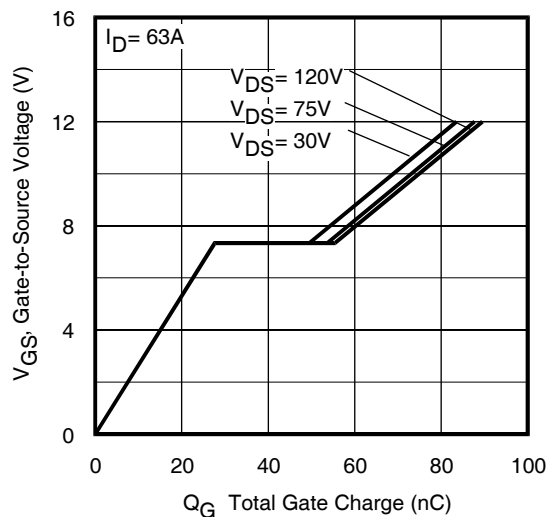
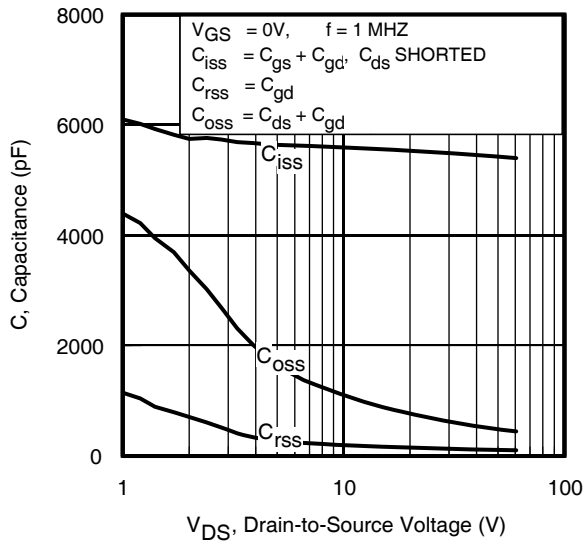
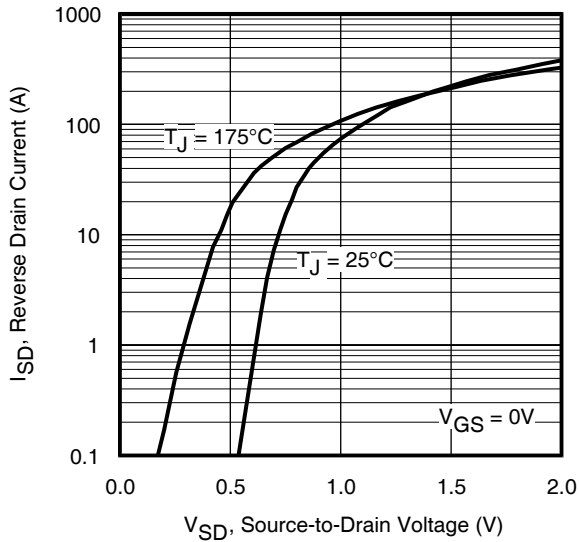
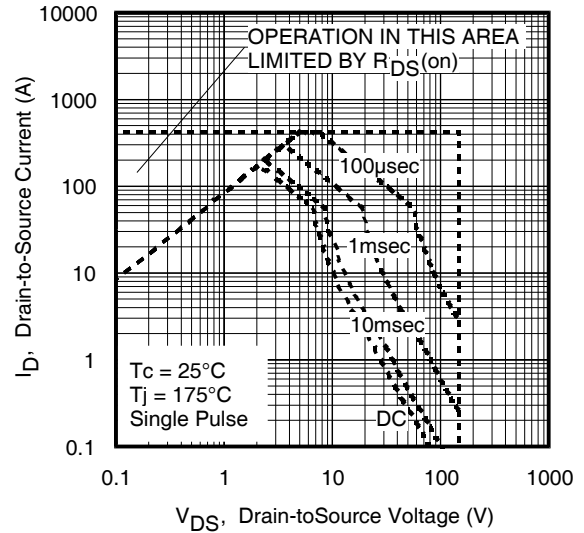


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

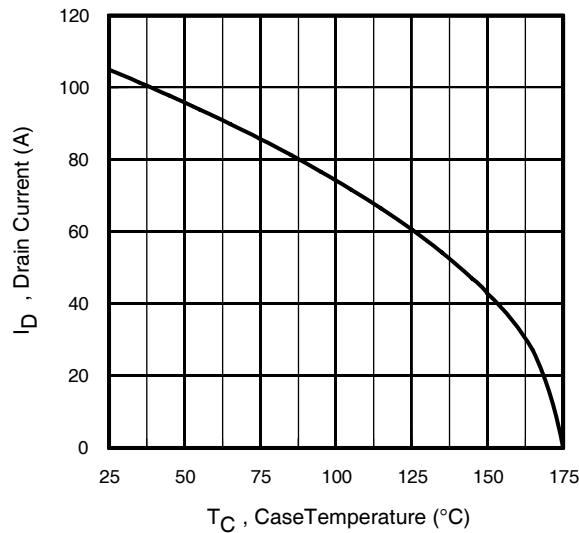
Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage



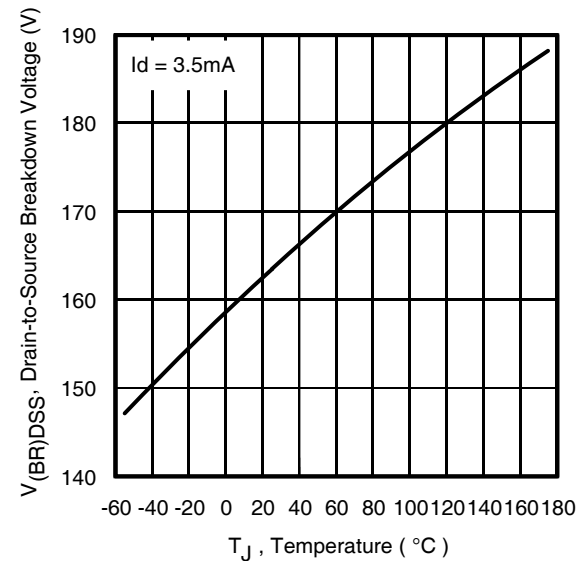
**Fig 7.** Typical Source-Drain Diode Forward Voltage



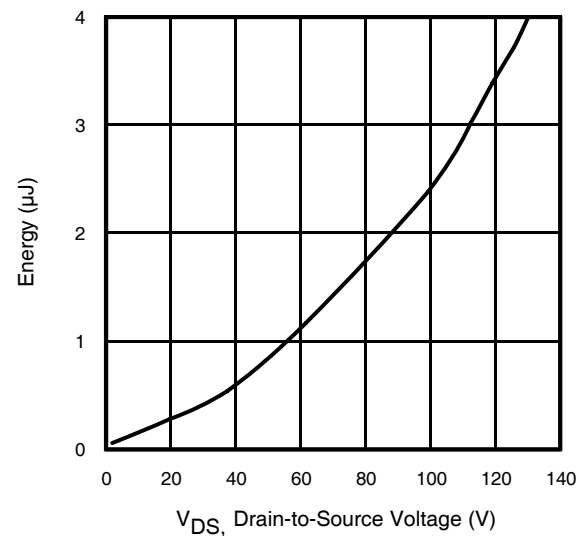
**Fig 8.** Maximum Safe Operating Area



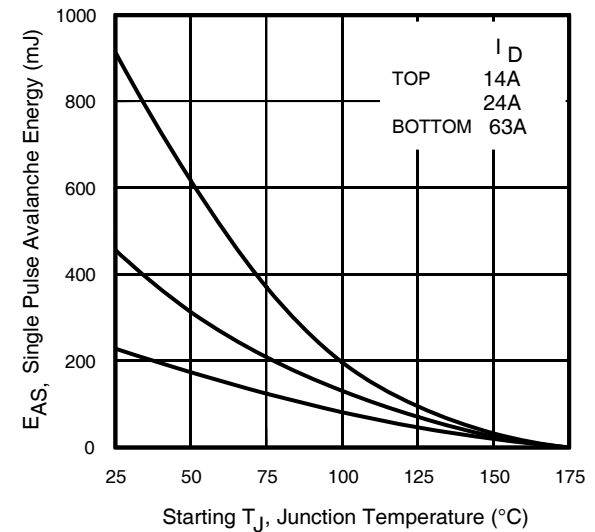
**Fig 9.** Maximum Drain Current vs. Case Temperature



**Fig 10.** Drain-to-Source Breakdown Voltage



**Fig 11.** Typical  $C_{OSS}$  Stored Energy



**Fig 12.** Maximum Avalanche Energy Vs. Drain Current

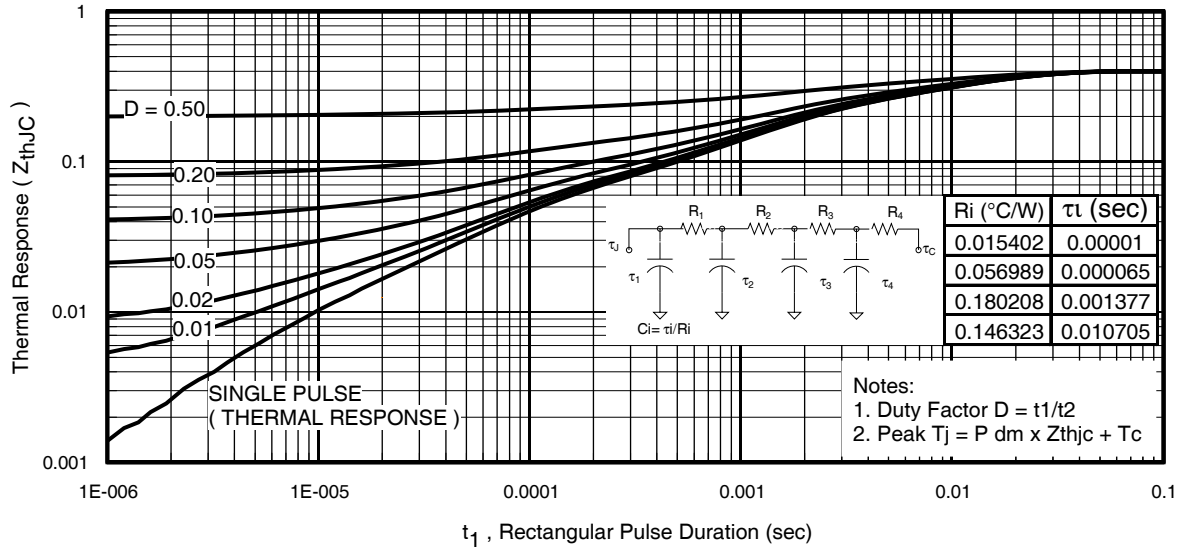


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

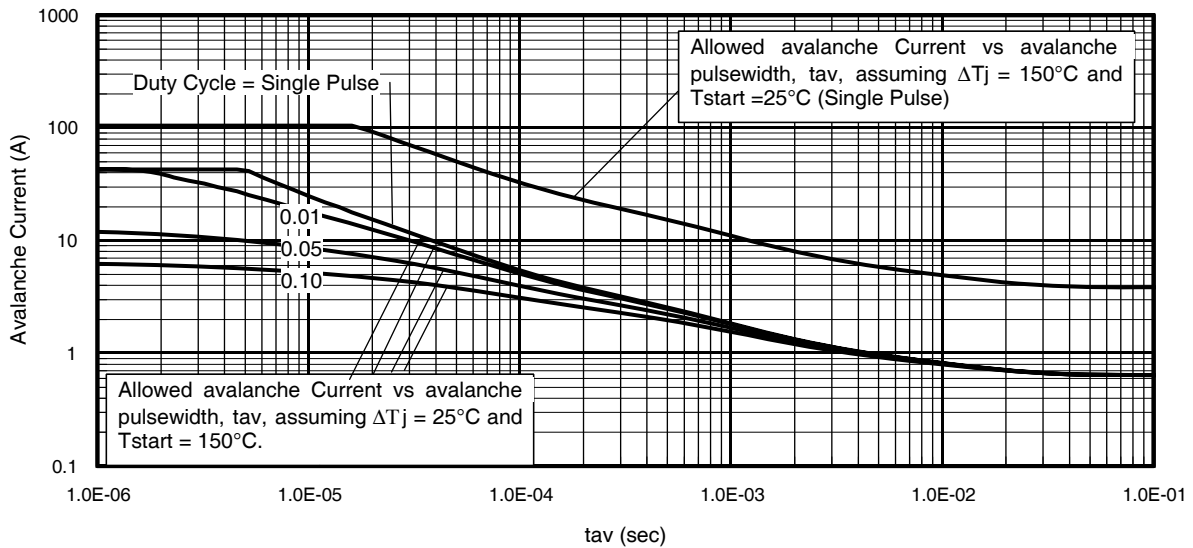
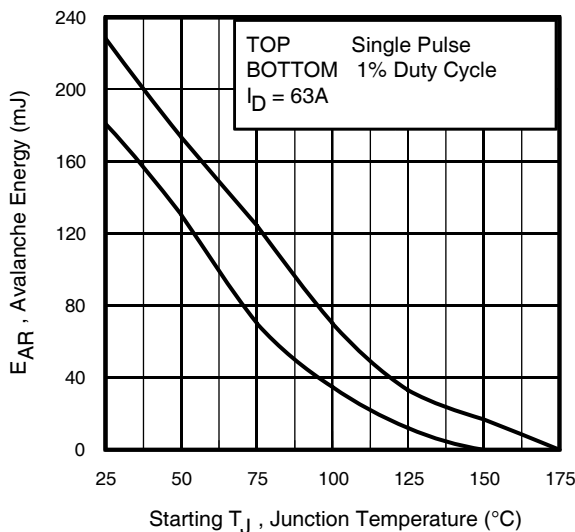


Fig 14. Typical Avalanche Current vs. Pulsewidth



**Notes on Repetitive Avalanche Curves, Figures 14, 15:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as  $25^{\circ}C$  in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

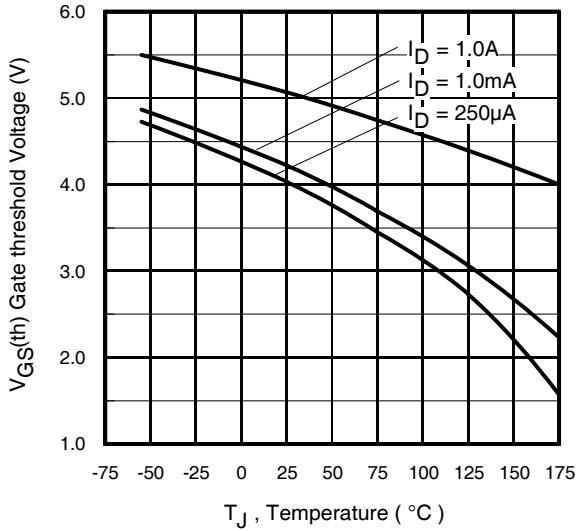


Fig 16. Threshold Voltage Vs. Temperature

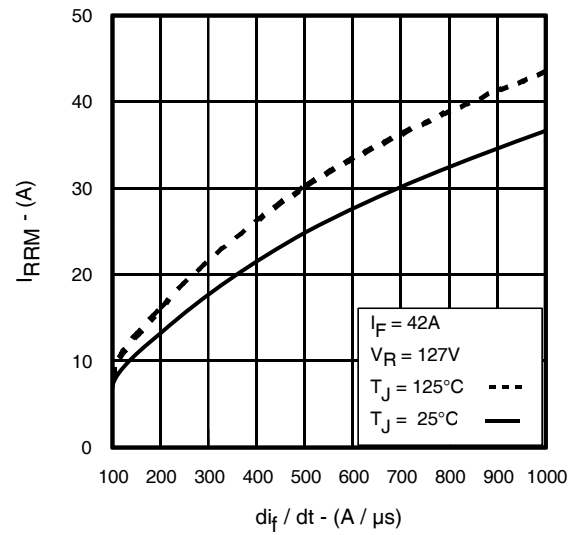


Fig. 17 - Typical Recovery Current vs. di<sub>f</sub>/dt

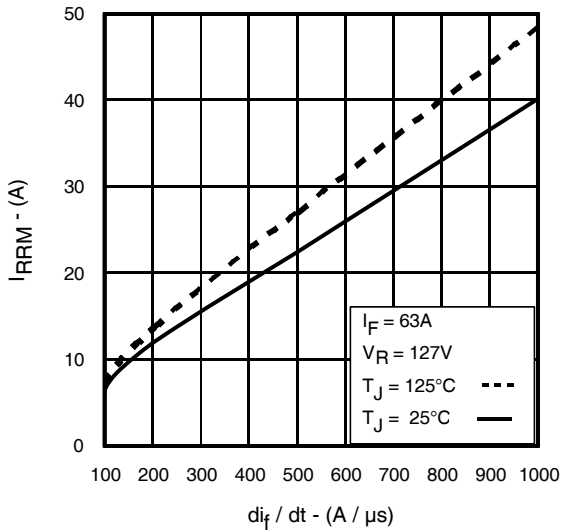


Fig. 18 - Typical Recovery Current vs. di<sub>f</sub>/dt

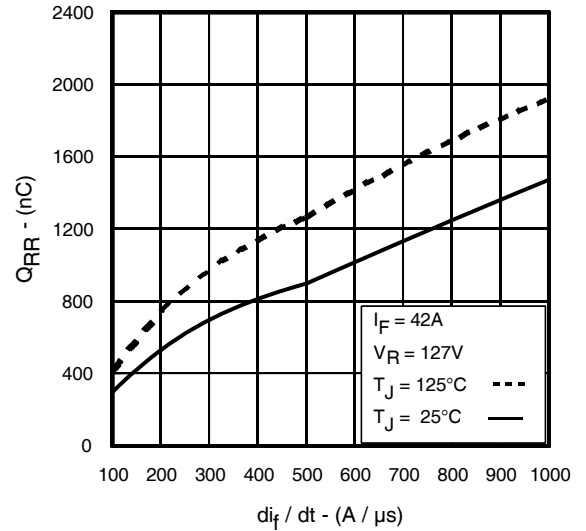


Fig. 19 - Typical Stored Charge vs. di<sub>f</sub>/dt

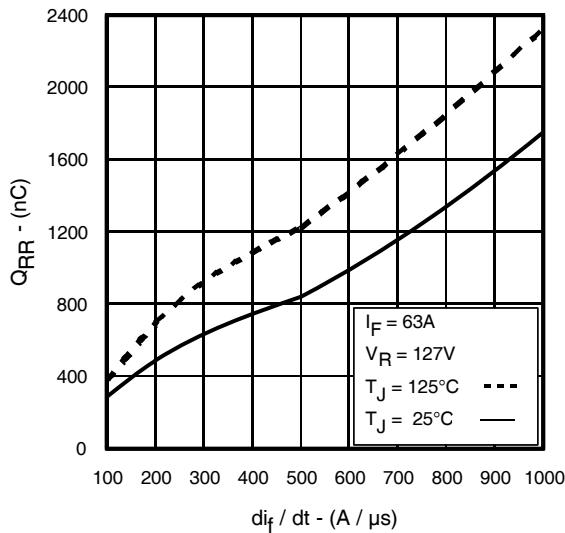
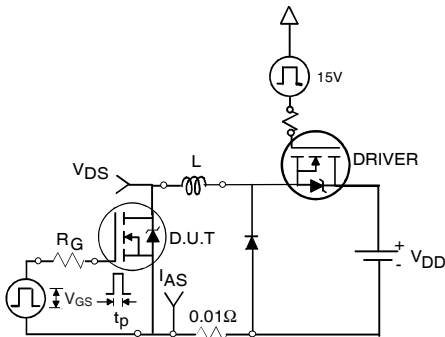


Fig. 20 - Typical Stored Charge vs. di<sub>f</sub>/dt



\*  $V_{GS} = 5V$  for Logic Level Devices

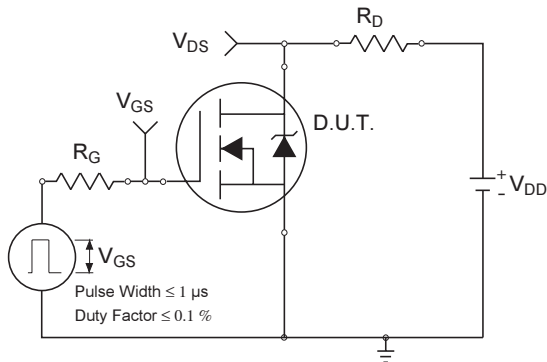
**Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**



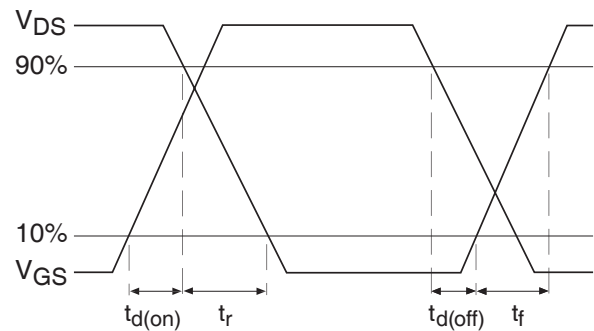
**Fig 22a. Unclamped Inductive Test Circuit**



**Fig 22b. Unclamped Inductive Waveforms**



**Fig 23a. Switching Time Test Circuit**



**Fig 23b. Switching Time Waveforms**



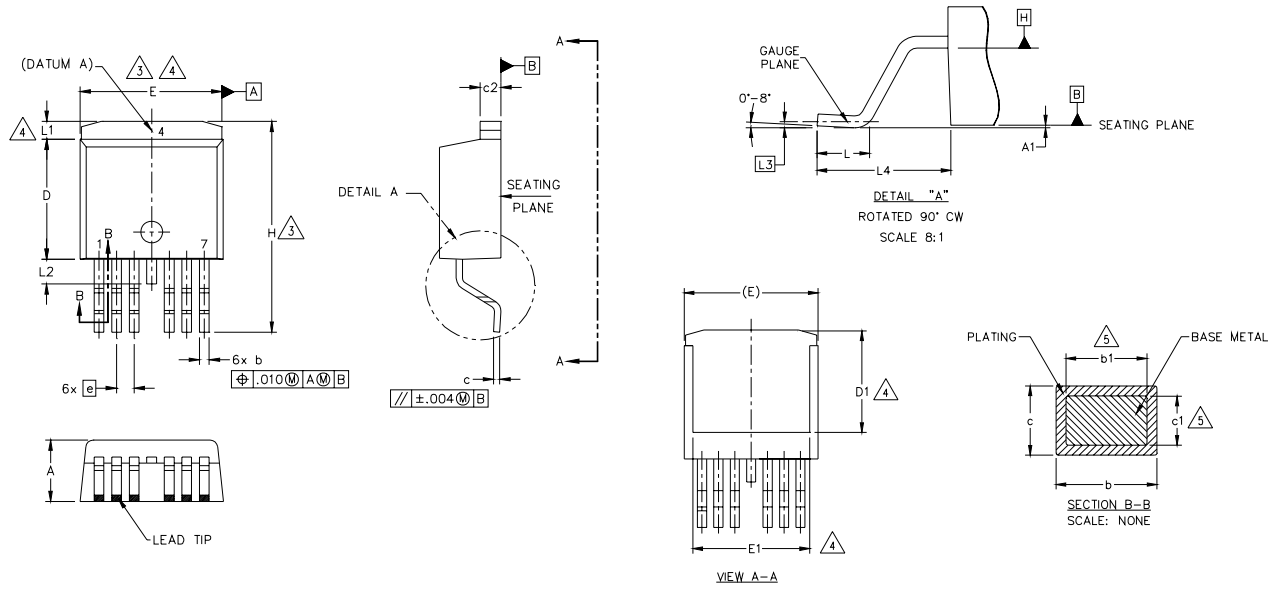
**Fig 24a. Gate Charge Test Circuit**



**Fig 24b. Gate Charge Waveform**

D<sup>2</sup>Pak - 7 Pin Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.06	4.83	.160	.190	5	
A1	—	0.254	—	.010		
b	0.51	0.99	.020	.036		
b1	0.51	0.89	.020	.032		
c	0.38	0.74	.015	.029		
c1	0.38	0.58	.015	.023		
c2	1.14	1.65	.045	.065		
D	8.38	9.65	.330	.380		3
D1	6.86	—	.270	—		4
E	9.65	10.67	.380	.420		3,4
E1	6.22	—	.245	—	4	
e	1.27 BSC		.050 BSC		4	
H	14.61	15.88	.575	.625		
L	1.78	2.79	.070	.110		
L1	—	1.68	—	.066		
L2	—	1.78	—	.070		
L3	0.25 BSC		.010 BSC			
L4	4.78	5.28	.188	.208		

NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263CB.

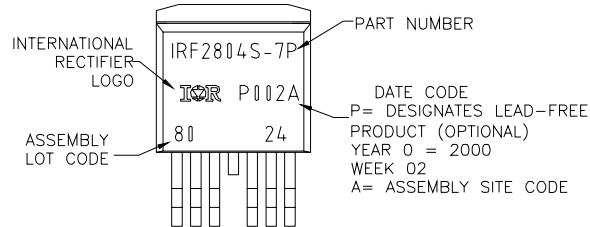
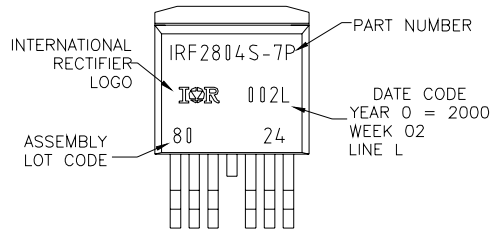
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



## D<sup>2</sup>Pak - 7 Pin Part Marking Information

EXAMPLE: THIS IS AN IRF2804S-7P WITH  
 LOT CODE 8024  
 ASSEMBLED ON WW02,2000  
 IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line  
 position indicates "Lead Free"

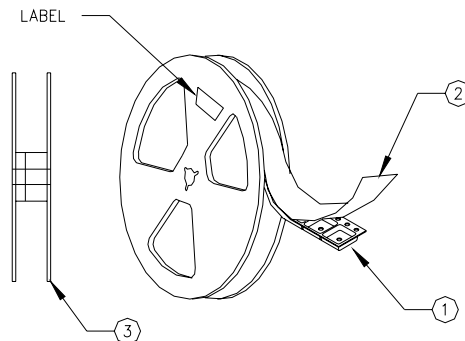
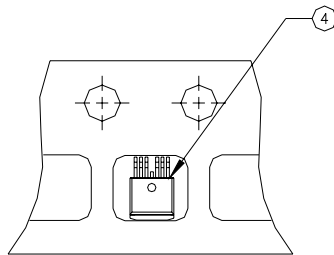


## D<sup>2</sup>Pak - 7 Pin Tape and Reel

NOTES, TAPE & REEL, LABELLING:

1. TAPE AND REEL.
  - 1.1 REEL SIZE 13 INCH DIAMETER.
  - 1.2 EACH REEL CONTAINING 800 DEVICES.
  - 1.3 THERE SHALL BE A MINIMUM OF 42 SEALED POCKETS CONTAINED IN THE LEADER AND A MINIMUM OF 15 SEALED POCKETS IN THE TRAILER.
  - 1.4 PEEL STRENGTH MUST CONFORM TO THE SPEC. NO. 71-9667.
  - 1.5 PART ORIENTATION SHALL BE AS SHOWN BELOW.
  - 1.6 REEL MAY CONTAIN A MAXIMUM OF TWO UNIQUE LOT CODE/DATE CODE COMBINATIONS. REWORKED REELS MAY CONTAIN A MAXIMUM OF THREE UNIQUE LOT CODE/DATE CODE COMBINATIONS. HOWEVER, THE LOT CODES AND DATE CODES WITH THEIR RESPECTIVE QUANTITIES SHALL APPEAR ON THE BAR CODE LABEL FOR THE AFFECTED REEL.

2. LABELLING (REEL AND SHIPPING BAG).
  - 2.1 CUST. PART NUMBER (BAR CODE): IRFXXXXSTRL-7P
  - 2.2 CUST. PART NUMBER (TEXT CODE): IRFXXXXSTRL-7P
  - 2.3 I.R. PART NUMBER: IRFXXXXSTRL-7P
  - 2.4 QUANTITY:
  - 2.5 VENDOR CODE: IR
  - 2.6 LOT CODE:
  - 2.7 DATE CODE:



**Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>**

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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